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Ho Jun Kim was born in Seoul, Korea, in 1980. He received B.S. degree in mechanical engineering from Hanyang University, Korea, in 2002, and M. S. and Ph.D. degrees in mechanical engineering from Texas A&M University, United States, in 2004 and 2008, respectively. From 2007 to 2008, he joined department of mechanical and aerospace engineering of Old Dominion University in United States, as a research associate. Since August 2008, he has been worked in Samsung Electronics as a senior engineer until 2014, and as a principal engineer until 2018 for Memory Thin Film Technology Team (CVD, PE-CVD, and PE-ALD). In March 2018, he joined Dong-A University as an assistant professor. His research interests include process plasma (CCP) simulations (PE-TEOS, PE-SiN, PE-SiON, ACL, and PE-ALD), process plasma (ICP) simulations (HDP-SiO₂, HDP-SiN, and HDP-ACL), thermal chemical vapor deposition (DCS-WSix, CVD-TiN, HARP-SiO₂, and BPSG), particle transport (contamination analysis and inertial particle modeling), remote plasma cleaning (fluorine chemistry, NF₃ plasma dissociation, fluorine transport, and surface chemistry), surface modeling (molecular dynamics, ab initio calculation, and computational chemistry), electro-deposition (turbulence analysis and electro chemistry), chemical mechanical polishing, chaotic transport in the micro fluidic devices (mixing, advection, and reaction). He was the recipient of Samsung Best Paper Award in 2013.